Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	230142	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:10
L2	105979	trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:10
L3	1857	L1 near2 L2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:10
L4	186219	inplant or implant or inplanting or implanting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:00
L5	21698	(chain$6 step$6 tier$4 multiple multi second! third) near2 L4 multi-implant$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:10
L6	330	L5 and L3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:10
L7	82	6 and (@ad < "19990422")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:04
L8	18924	4 same (ev electronvolt electron adj volt energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:13
L9	37	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18
L10	3	"6750507".pn. or "6413822".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 16:18

L11	4215	((438/270) or (438/272) or (438/268) or (438/514) or (438/527)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/16 18:00
L12	239	williams-richard-k.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:00
L14	18	grabowski-wayne.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:02
L15	63	(advanced adj analogic).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:02
L16	68	(12 14 15) and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:03
L17	28	(12 14 15) and 5 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:03
L18	8	17 and (@ad < "19990422")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 18:05